

### isc N-Channel MOSFET Transistor

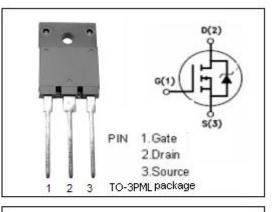
# 2SK1464

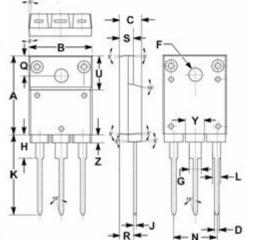
#### DESCRIPTION

- Drain Current –I\_D=8A@ T\_C=25 $^\circ\!\!\mathrm{C}$
- Drain Source Voltage-
- : V<sub>DSS</sub>=900 (Min)

**APPLICATIONS** 

 Minimum Lot-to-Lot variations for robust device performance and reliable operation





ABSOLUTE MAXIMUM RATINGS(Ta=25°C)	ABSOLUTE	MAXIMUM	RATIN	GS(T <sub>a</sub> =25	C)
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motor controls, relay and solenoid drivers.

SYMBOL	ARAMETER	VALUE	UNI T
V <sub>DSS</sub>	Drain-Source Voltage (V <sub>GS</sub> =0)	900	V
$V_{GS}$	Gate-Source Voltage	±30	v
ID	Drain Current-continuous@ TC=25℃	8	A
P <sub>tot</sub>	Total Dissipation@TC=25°C	80	w
Tj	Max. Operating Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C

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• Designed especially for high voltage, high speed applications,

such as off-line switching power supplies , UPS,AC and DC

nation	m	mm		
DIM	MIN	MAX		
Α	19.90	20.10		
В	15.90	16.10		
C D	5.50	5.70		
D	0.90	1.10		
F	3.30	3.50		
G	2.90	3.10		
H	5.90	6.10		
J	0.595	0.605		
K	22.30	22.50		
L	1.90	2.10		
N	10.80	11.00		
0	4.90	5.10		
R	3.75	3.95		
S	3.20	3.40		
U	9.90	10.10		
Y	4.70	4.90		
Z	1.90	2.10		



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SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0; I <sub>D</sub> = 10mA	900			V
$V_{GS(th)}$	Gate Threshold Voltage	V <sub>DS</sub> =10V; I <sub>D</sub> =1mA	2.0		3.0	V
R <sub>DS(on)</sub>	Drain-Source On-stage Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =4A		1.2	1.6	Ω
I <sub>GSS</sub>	Gate Source Leakage Current	V <sub>GS</sub> = ±30V;V <sub>DS</sub> =0			±100	nA
IDSS	Zero Gate Voltage Drain Current	V <sub>DS</sub> =900V; V <sub>GS</sub> = 0			1	mA
$V_{\text{SD}}$	Diode Forward Voltage	I <sub>F</sub> =8A; V <sub>GS</sub> =0			1.8	V
tr	Rise time			80		ns
ton	Turn-on time	V <sub>GS</sub> =10V;I <sub>D</sub> =4A;R∟=50 Ω		100		ns
tf	Fall time			150		ns
toff	Turn-off time	1		500		ns

#### • ELECTRICAL CHARACTERISTICS (Tc=25°C)

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